



# Innovations in Testing for Truly Known Good High Bandwidth Memory Stacks



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# Agenda

- **Advanced Packaging Market Trend and Complexity Trend**
- **High Bandwidth Memory and SoC Die Yield Impact Analysis**
- **HBM Test Insertion and Known Good Die test method Discussion**
- **Die Carrier + Advantest Handler Test solution**
  - DC thermal performance
  - Electrical performance (SI/PI) simulation result
  - Scrub mark and contact repeatability study
  - Die level KGD test scalability roadmap
- **Summary, Acknowledgement**

# Advanced Packaging Market Trend

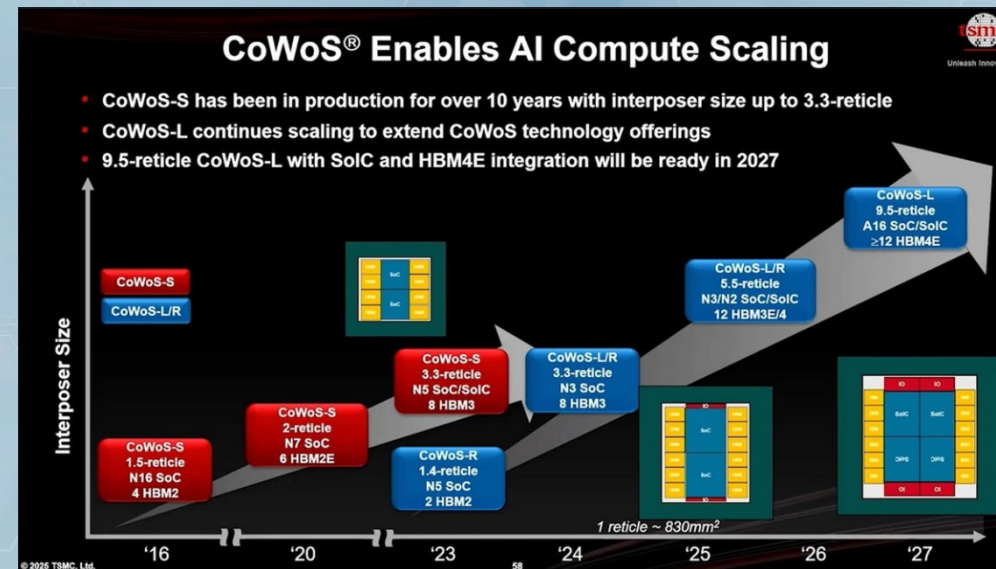
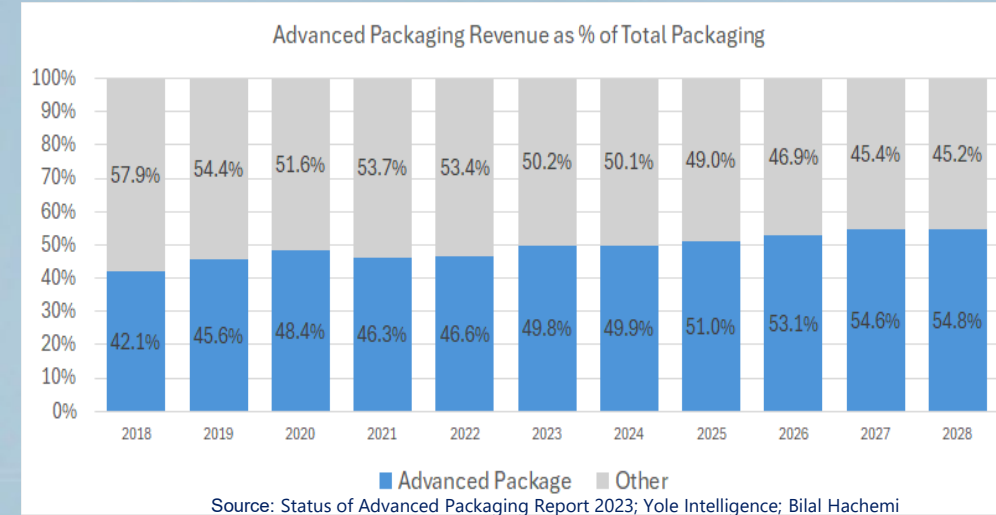
Forecasted 2025 >50% IC fab by Advanced Packaging

- **Advanced Packaging Revenue Growth of CARRG 12.7% as a Percent of Total Packaging Revenue ('18 – '28)**

- More chips in the package → higher values being added
- Advanced Packaging offers more features & computing power than individual IC packages – driving market growth

- **Advanced Packaging Complexity Trend:**

- 1 SoC + 4 HBM → 4 SoC + >12 HBM
- HBM Core stack: 4 → 16
- Package size 1.5 → 9.5 reticle: increasing number of transistors and they all need to be tested

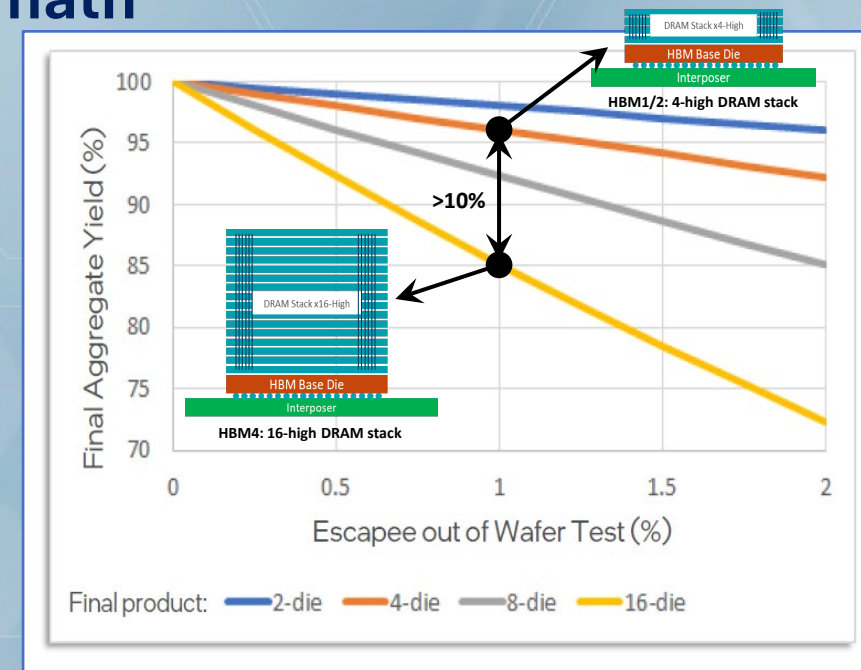


# Advanced Packaging Demanding More KGD Test

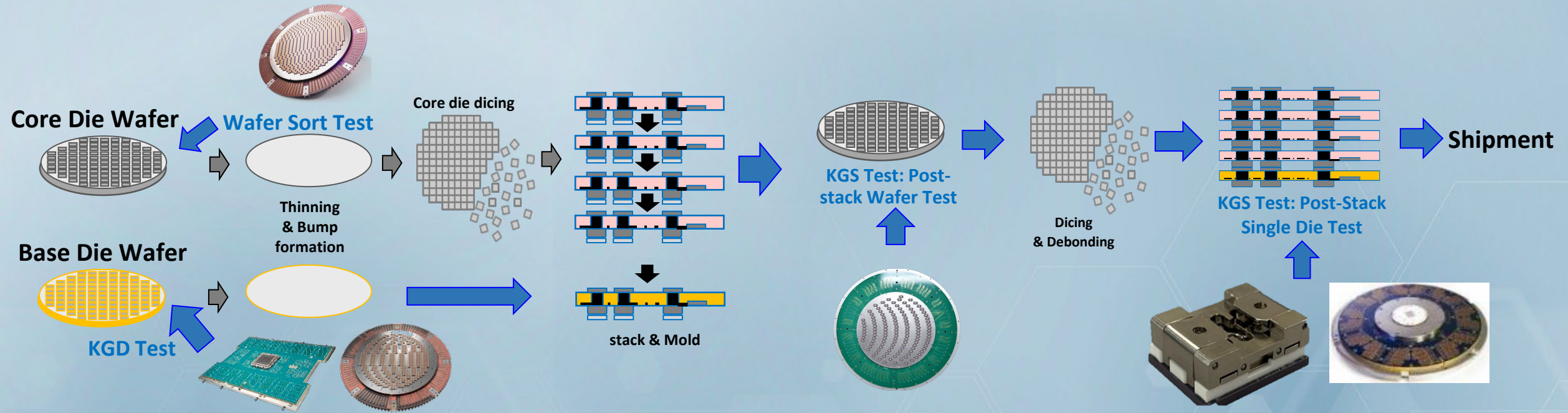
- **Multi-chiplet products require near-Known Good Die constituent chiplets**
  - This requirement becomes more important as the number of chiplets in the chip increases
- **Matching of constituent performance bins is also important**
  - Performance of the multi-chiplet System-in-Package is determined by the lowest-performance chiplet in the stack
  - Limits selling price in performance applications
- **Cost vs. test coverage optimization comes down to math**
  - Earlier defect detection helps save packaging costs
  - Higher complexity → high packaging costs
  - Higher complexity → lower yields

Wafer Test Coverage			
Die Yield	High	Zero	Some
	Low	Some	Lots
		Low	High
		Packaging Cost	

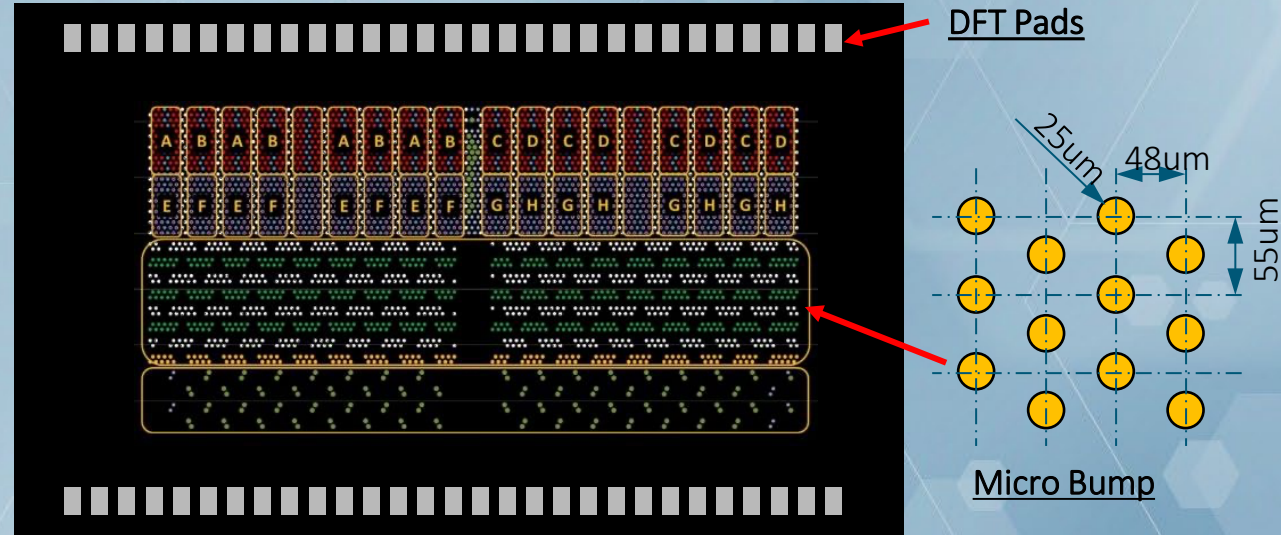
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# High Bandwidth Memory Test Flow & Challenges

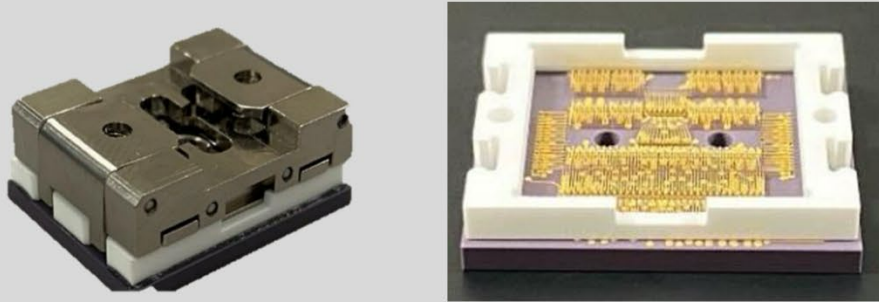


	Micro-bump probing test	DFT pad probing test
<b>Pros</b>	<ul style="list-style-type: none"> <li>Best test coverage</li> <li>Real performance data</li> </ul>	<ul style="list-style-type: none"> <li>No damage to ubumps</li> <li>Highest test efficiency</li> </ul>
<b>Cons</b>	<ul style="list-style-type: none"> <li>Connection reliability concern on ubump</li> <li>Low test efficiency</li> <li>High test cost</li> </ul>	<ul style="list-style-type: none"> <li>DFT required design in HBM</li> <li>Test coverage gap</li> </ul>



# HBM test cell solution by “Die Carrier”

➤ Die Carrier (Interposer, Lid, Probe)



➤ Inserter/Remover



# Key Challenging on Current Test Process

## KGS Test: Post-stack Wafer Test



### Post-stack Wafer Test



Test efficiency:

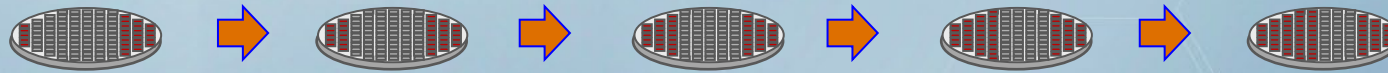
80%

75%

70%

65%

60%



- ✓ Failure Die is carried together to next test process
- ✓ Test efficiency becomes getting worse along with each test process
- ✓ Need multiple contact for retest/each test processes (mechanical stress)

### Post-stack Single Die Test



Test efficiency:

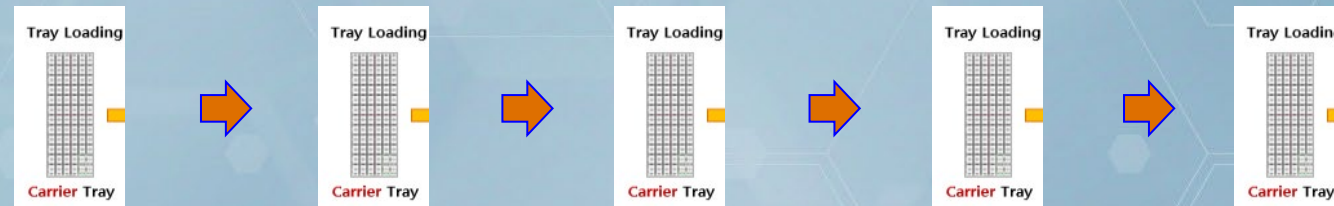
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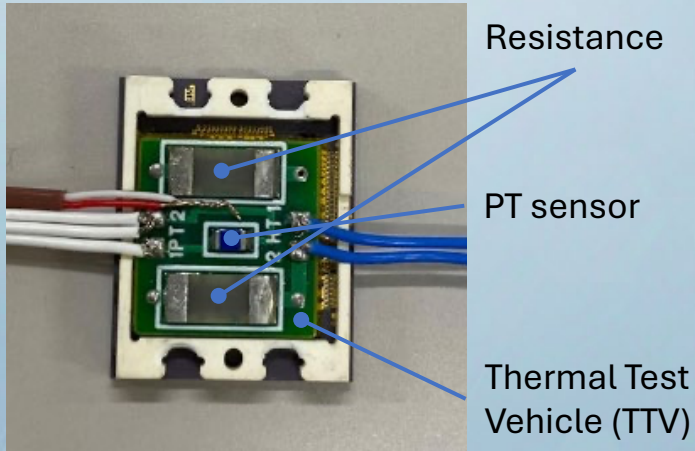
100%

100%



- ✓ **Failure Die can be rejected** on each test processes
- ✓ Test efficiency can keep **100%** (larger through put)
- ✓ Only **1-insertion** (pack into die carrier) during entire test processes (less mechanical stress)

# DC Thermal Structure Overview



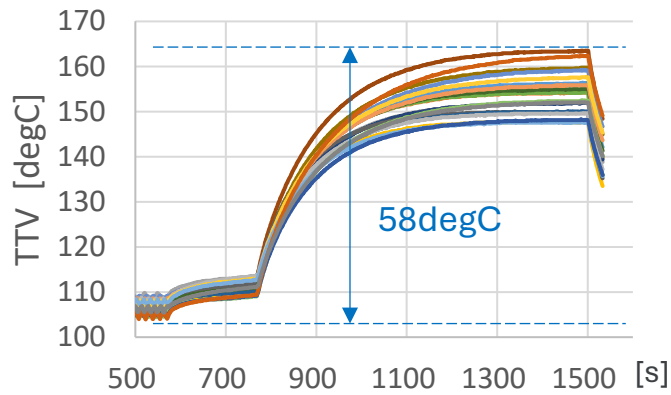
Current handler



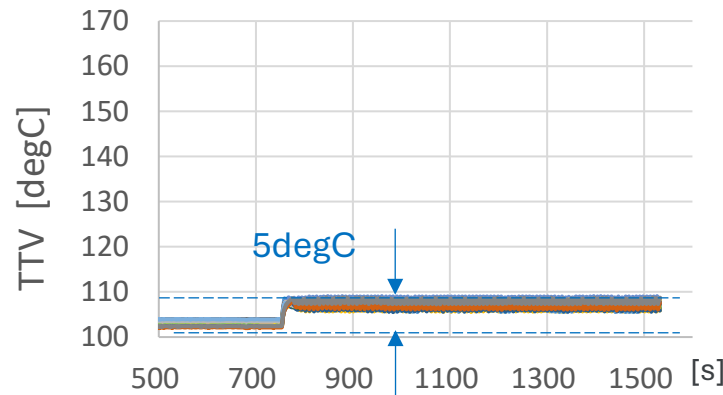
Next Gen

New Gen handler

## ➤ TTV temperature rise comparison w/ 2.2w heat generation



without T-pusher control

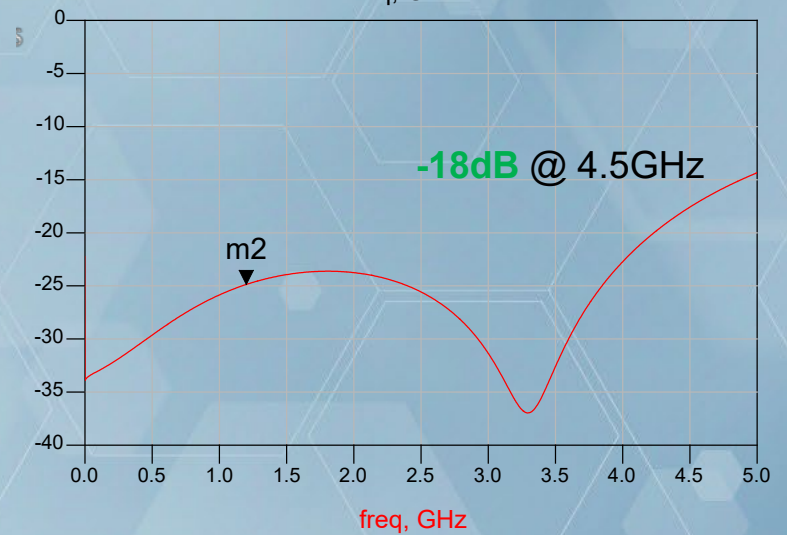
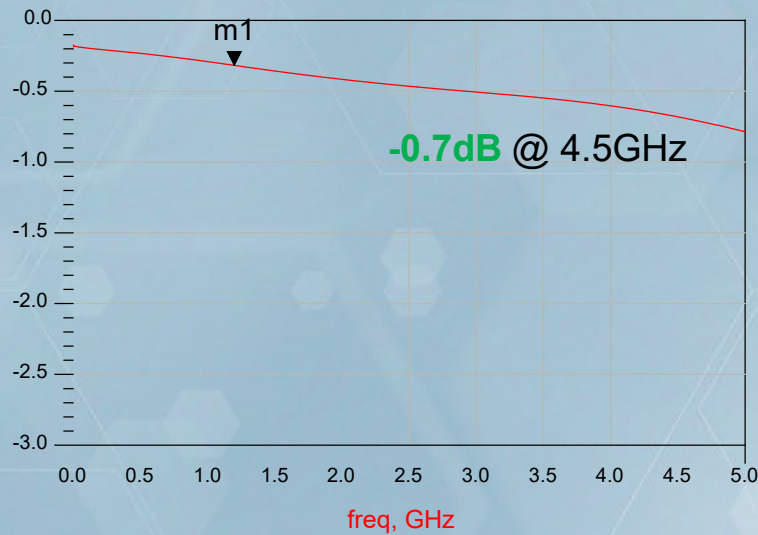
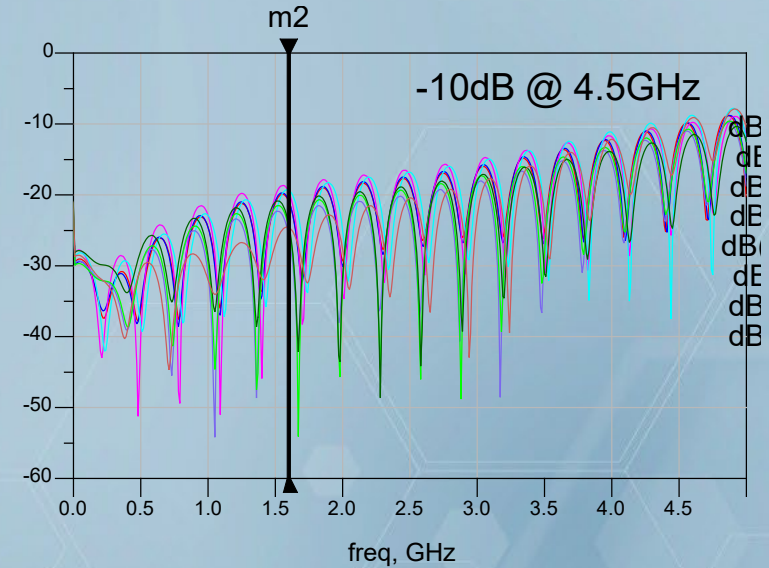
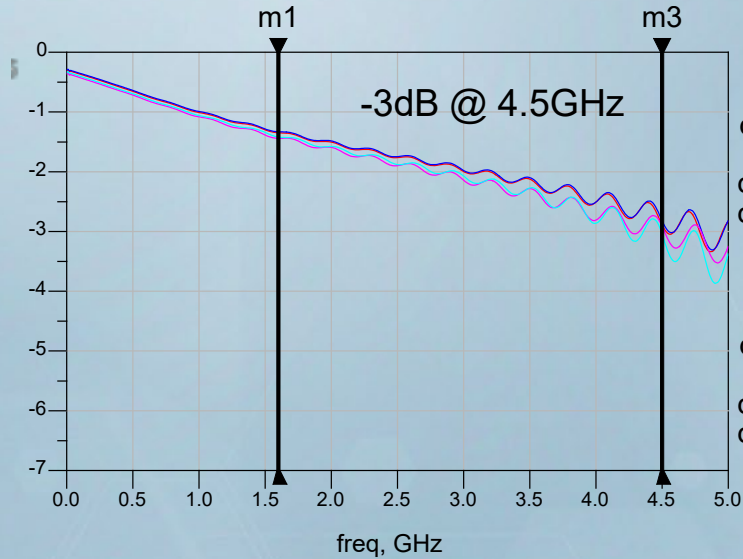
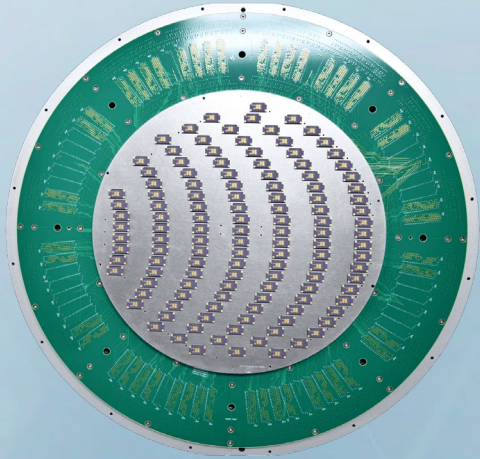


with T-pusher control

Item	Thermal Performance		
Handler	Current	Next Gen	
Parallelism	64	128	256
Heat generation	2.2W	40W	20W
temperature	105°C	105°C	
Tj rise(all Die)	≤5°C	≤3°C	

# Die Carrier: >2x Better Electrical Performance

By Eliminate >200mm PCB Trace



# Carrier Structure and SI/PI Simulation Result

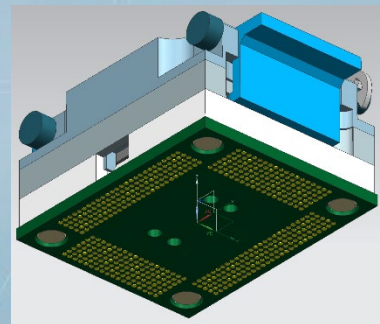
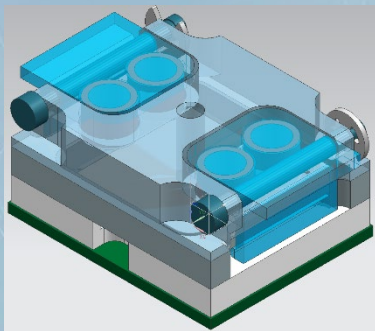
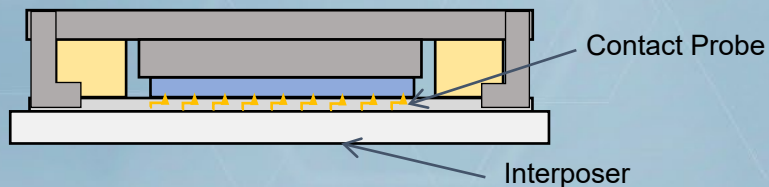
## Carrier structure

### ➤ Structure

- Contact to HBM device : MEMS Probe
- Contact to test socket : Interposer

### ➤ Pros

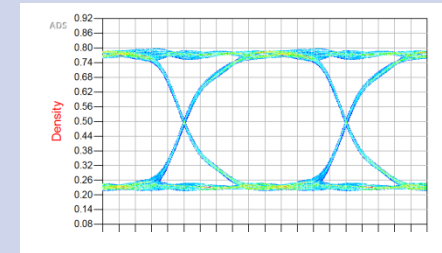
- High electrical performance can be expected
- Similar pad scrub behavior with wafer test



## SI/PI Simulation result

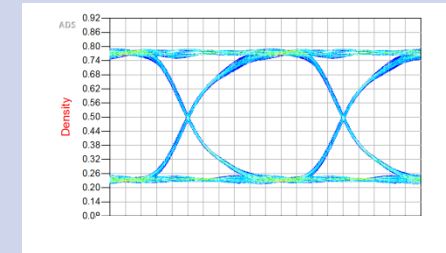
2.0Gbps ODT\_50

Eye height opening rate : 92.8%



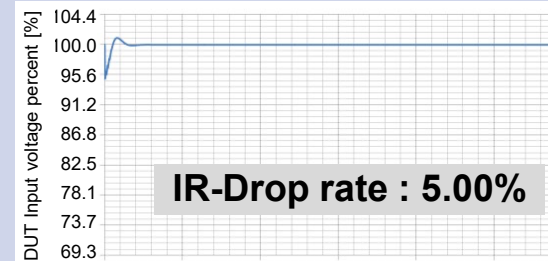
2.4Gbps ODT\_50

Eye height opening rate : 90.1%

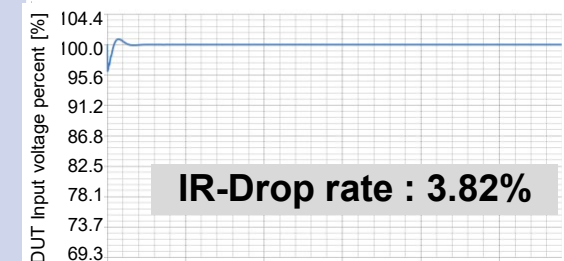


T5503HS2 DUT's Input signal (Write cycle)

C(k) setting : C(2)



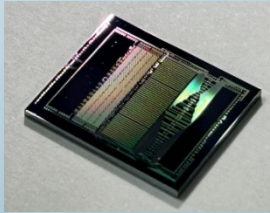
C(k) setting : C(4)



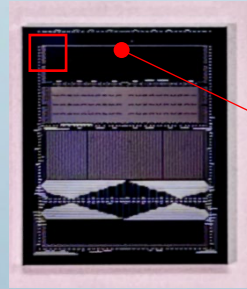
T5503HS2 Power supply simulation (IR-Drop) results in 64DUT

# Die carrier Repeatability Evaluation Results

Dummy Die  
11 x 13 x 0.8mm



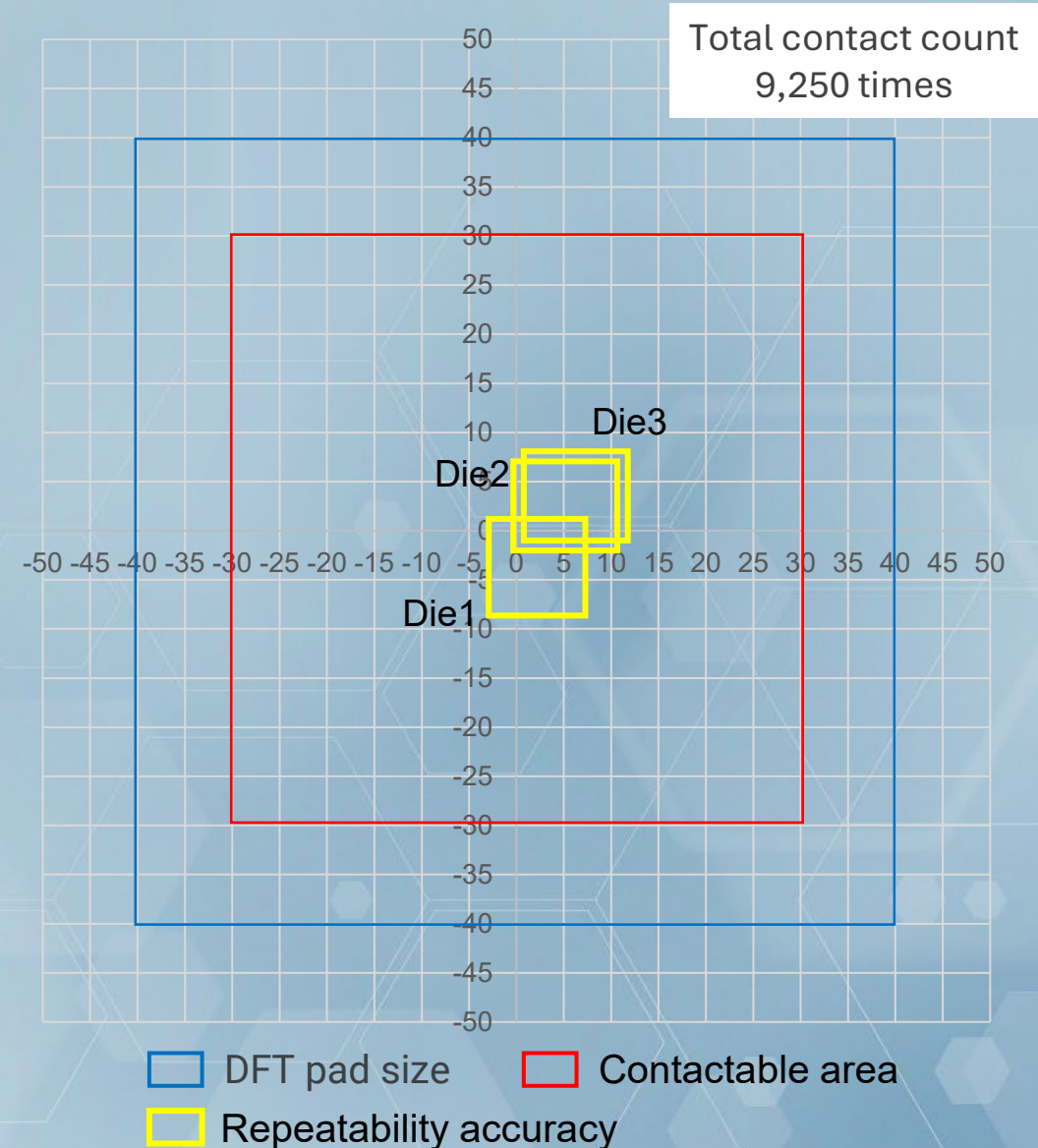
Front view



DFT pad 505pcs

Count	Sample 1	Sample 2	Sample 3
100			
500			
Final	1,100 	6,600 	1,550 

DFT pad  
80umx80um



# Die Level Test Solution Scalability



## Manual Test

1. Using Engineering system for validation
2. Using **Manual JIG** for die insert
3. Correlation between Wafer Test and Die level test @RT



## HVM @RT

1. Using Die Carrier solution for HVM @RT
2. Using **Inserter/Remover** for die insert
2. Correlation between Manual and HVM



## HVM@HT

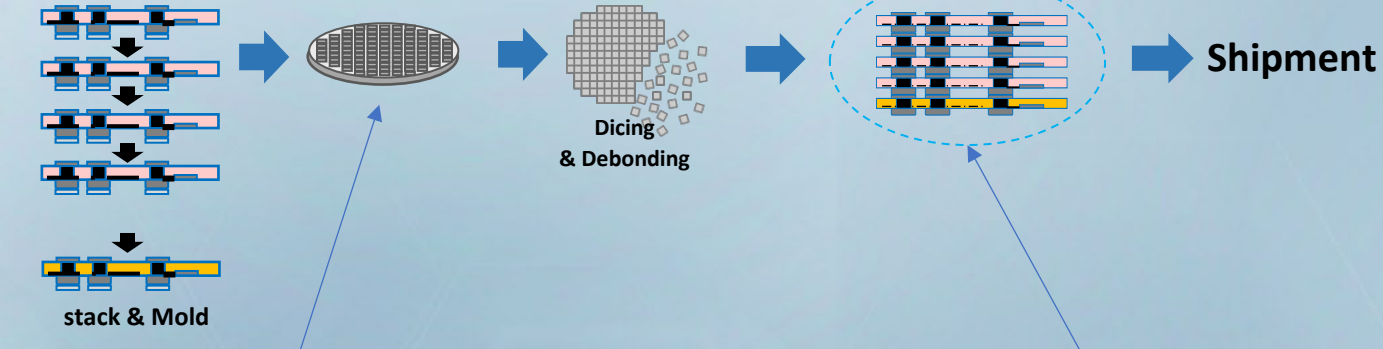
1. Using Die Carrier solution for HVM @HT
2. Using **Inserter/Remover** for die insert
3. Correlation between RT and HT



**Inserter/Remover**

# HBM Singulated Stack Die Test Solution

HBM Stacking Process



## Post-stack Wafer Test



## Post-stack Single Die Test



## Product Features:

- Compatible with conventional probe
- Offer same high-speed performance as HFTAP\*
- Cold and Hot temperature capability
- Design with Advantest handler and tester build in vision alignment feature

\*HFTAP : High Frequency Test At Probe

## Product Benefits:

- Offer **truly** known good stack/die test solution
- Enable quality screening post HBM stack wafer dicing
- HBM KGD test capability up to **4GHz**
- High parallelism test (limited to handler and tester resource)
- Excellent thermal control up to **40W**
- Keep **100% test efficiency** with removing failure die
- **1-insertion** during entire test flow (less stress)
- Engineering/HVM setup ready

# Summary

## Technical Advantage – Die-Level Testing

- Singulated die testing allows full-speed, multi-temperature screening before stacking
- 1-insertion via die carrier achieves complete test coverage (DC, functional, etc.) in a single insertion
- Supports high parallelism, improving overall throughput without compromising test quality
- Engineering setup to HVM scalability

## Scalability and Future Applications

- The short transmission path of the die carrier architecture enables reliable multi-GHz test performance
- Well suited for wafer-level high-speed memory testing and future chiplet architectures

# Acknowledgement

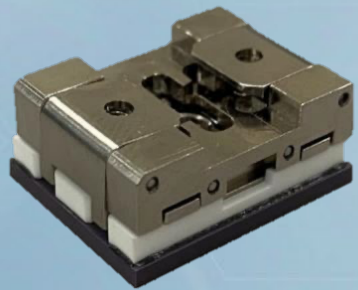
- **FormFactor**

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- Jim Tseng
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- Mitsunori Aizawa
- Atsushi Nakadate

# Questions?



# Thank you